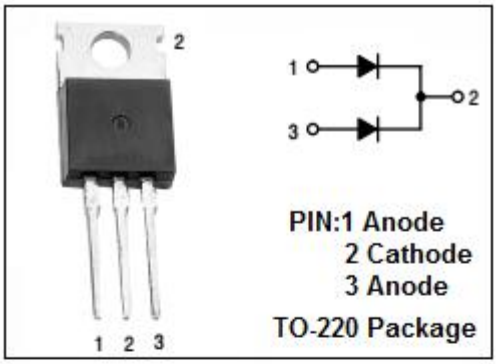
Schottky Barrier Rectifier — MBR20H150CT

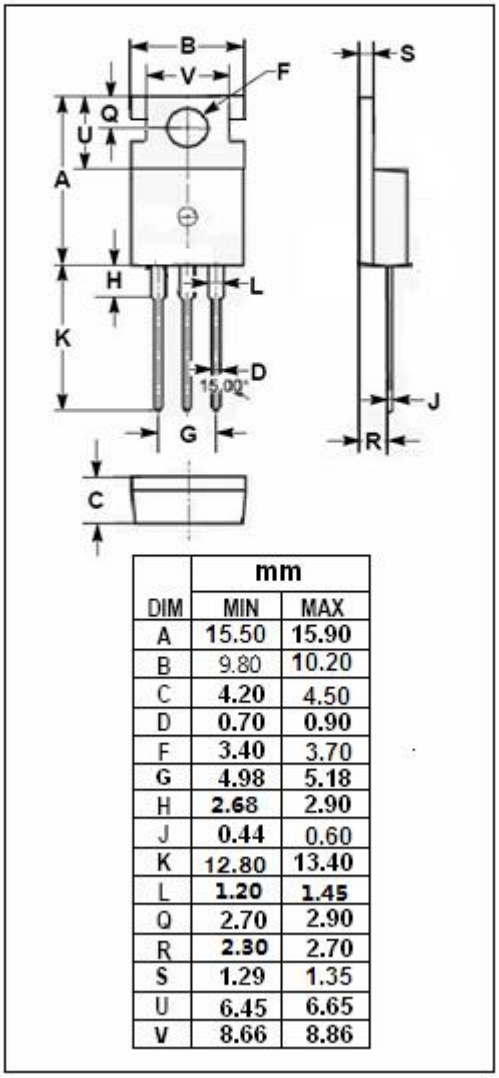
FEATURES

- Dual rectifier construction，positive center tap
- Low Power Loss,High Efficiency
- Guard ring for overvoltage protection
- Metal of silicon rectifier, majonty carrier conduction
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



APPLICATIONS

- For use in high frequency inverters,free wheeling and polarity protection applications.



DIM	mm MIN	mm MAX
A	15.50	15.90
B	9.80	10.20
C	4.20	4.50
D	0.70	0.90
F	3.40	3.70
G	4.98	5.18
H	2.68	2.90
J	0.44	0.60
K	12.80	13.40
L	1.20	1.45
Q	2.70	2.90
R	2.30	2.70
S	1.29	1.35
U	6.45	6.65
V	8.66	8.86

ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{RRM} V_{RMS} V_R	Peak Repetitive Reverse Voltage RMS Voltage DC Blocking Voltage	150	V
$I_{F(AV)}$	Average Rectified Forward Current	10	A
I_{FSM}	Nonrepetitive Peak Surge Current 8.3ms single half sine-wave superimposed on rated load conditions	200	A
I_{RRM}	Peak Repetitive Reverse Surge Current (2μs, 1.0kHz)	1.0	A
T_J	Junction Temperature	175	℃
T_{stg}	Storage Temperature Range	-65~175	℃
dv/dt	Voltage Rate of Change (Rated V_R)	10,000	V/μs

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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance,Junction to Case	2.2	℃/W

ELECTRICAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	MAX	UNIT
V_F	Maximum Instantaneous Forward Voltage	I_F= 10A ; Tc 25℃	0.90	V
		I_F= 10A ; Tc= 125℃	0.75	
		I_F= 20A ; Tc= 25℃	0.99	
		I_F= 20A ; Tc= 125℃	0.86	
I_R	Maximum Instantaneous Reverse Current	V_R= $V_{RWM;}$Tj= 25℃	5.0	uA
		V_R= $V_{RWM;}$Tj= 125℃	1.0	mA